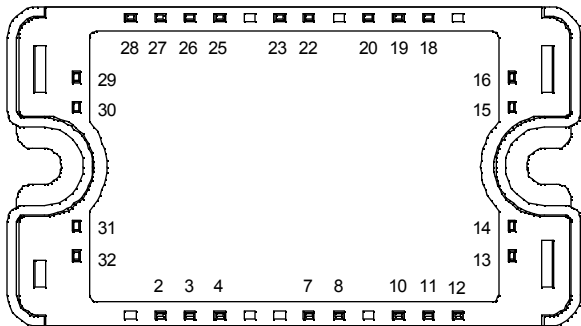
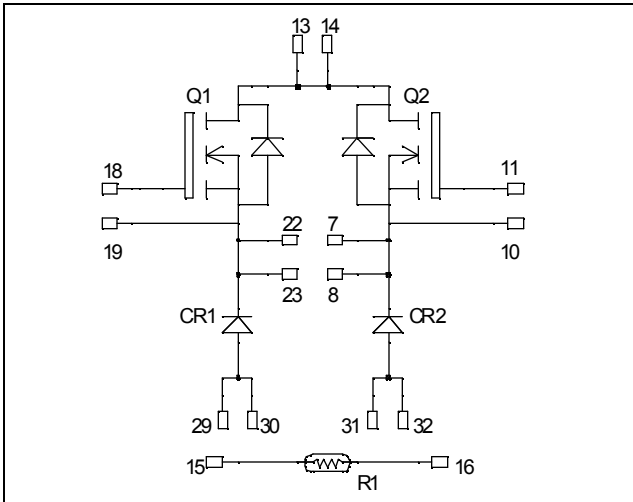


## Dual Buck chopper MOSFET Power Module

$V_{DSS} = 100V$   
 $R_{DSon} = 9m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 139A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Power MOS V<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	100	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	139
		$T_c = 80^\circ C$	100 *
$I_{DM}$	Pulsed Drain current	430	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	9.5	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	390
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

\* Specification of MOSFET device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$			100	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 80V$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 69.5A$		9	9.5	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	2		4	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 100$	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		9875		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		3940		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		1470		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 50V$ $I_D = 139A$		350		nC
$Q_{gs}$	Gate – Source Charge			60		
$Q_{gd}$	Gate – Drain Charge			180		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V$ $V_{Bus} = 66V$ $I_D = 139A$ $R_G = 5\Omega$		35		ns
$T_r$	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			95		
$T_f$	Fall Time			125		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 139A, R_G = 5\Omega$		552		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy ❷			604		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 139A, R_G = 5\Omega$		608		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy ❷			641		

❶  $E_{on}$  includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

## Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200V$	$T_j = 25^\circ\text{C}$		250	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle		100		A
$V_F$	Diode Forward Voltage	$I_F = 100A$		1		V
		$I_F = 200A$		1.4		
		$I_F = 100A$	$T_j = 125^\circ\text{C}$		0.9	
$t_{rr}$	Reverse Recovery Time	$I_F = 100A$ $V_R = 133V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		60	ns
			$T_j = 125^\circ\text{C}$		110	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 100A$ $V_R = 133V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		200	nC
			$T_j = 125^\circ\text{C}$		840	

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case	IGBT		0.32	°C/W	
		Diode		0.55		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1 mA, 50/60 Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	1.5	4.7	N.m
Wt	Package Weight				110	g

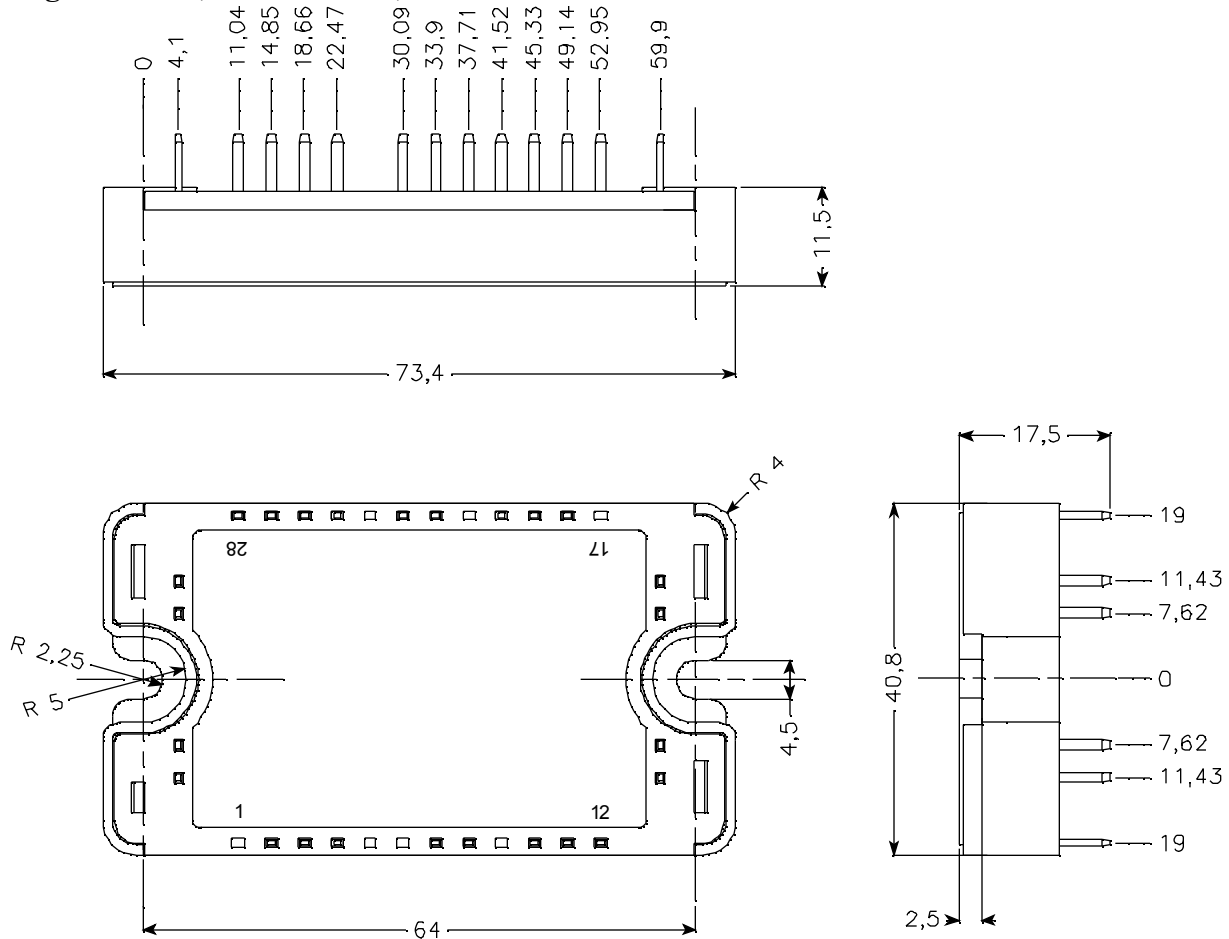
**Temperature sensor NTC** (for more information see application note APT0406 on [www.advancedpower.com](http://www.advancedpower.com)).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

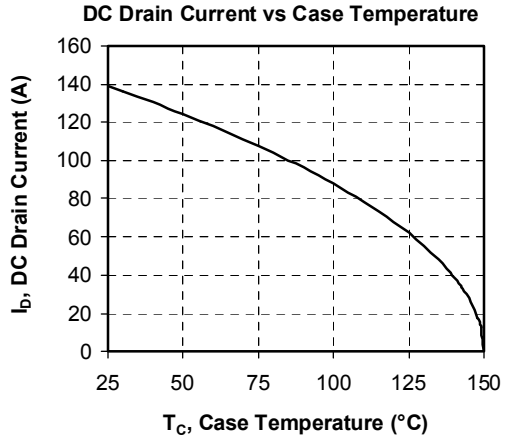
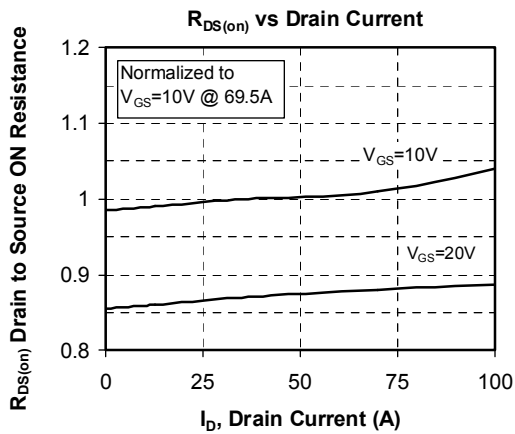
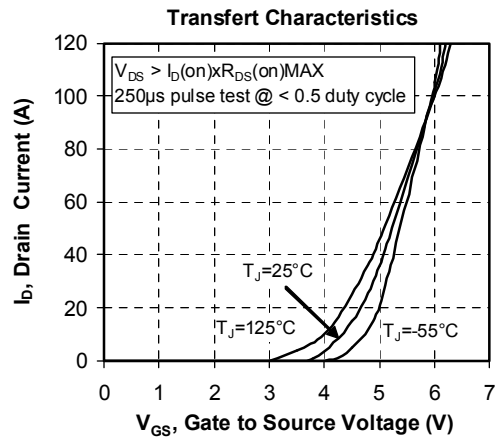
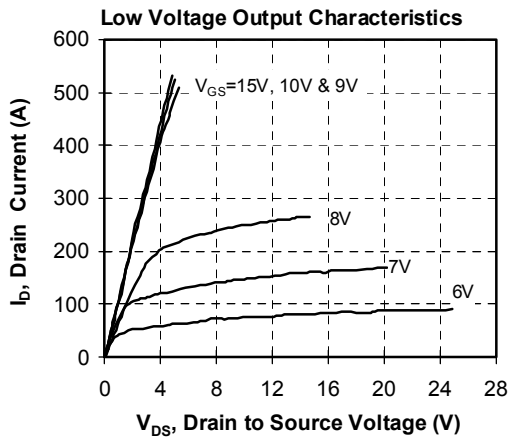
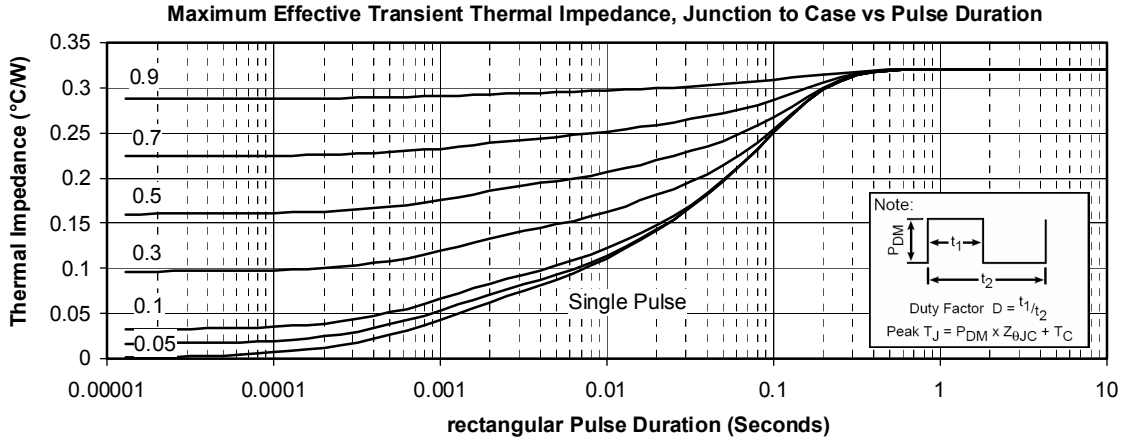
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85} \left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

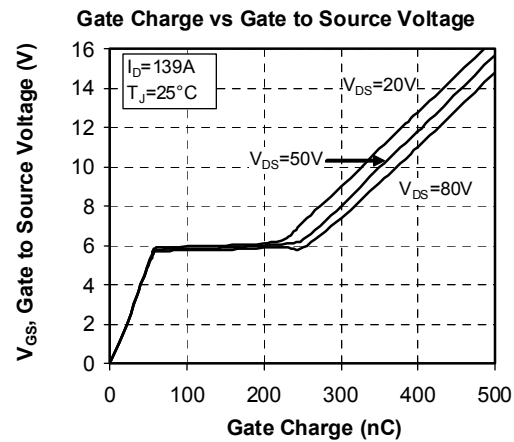
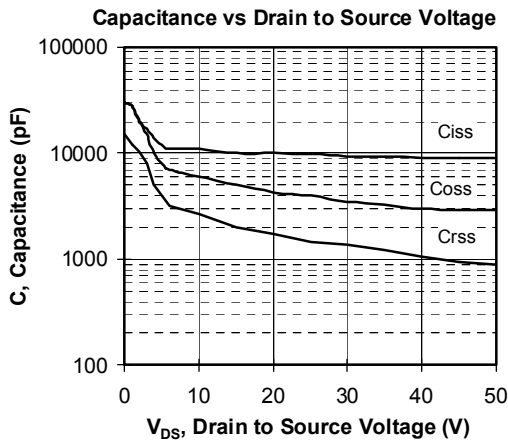
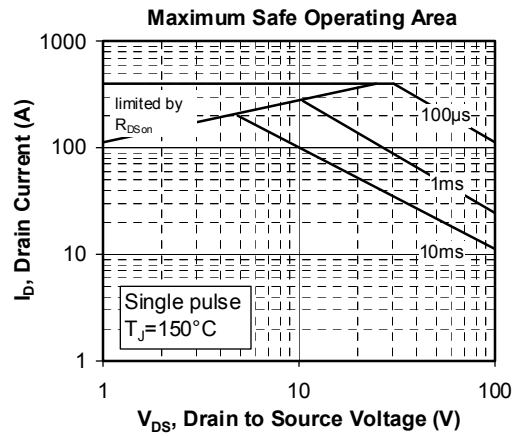
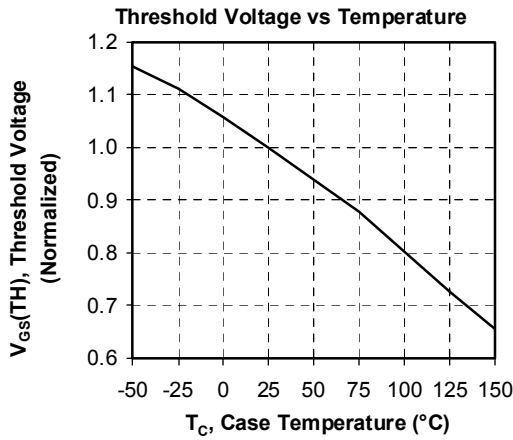
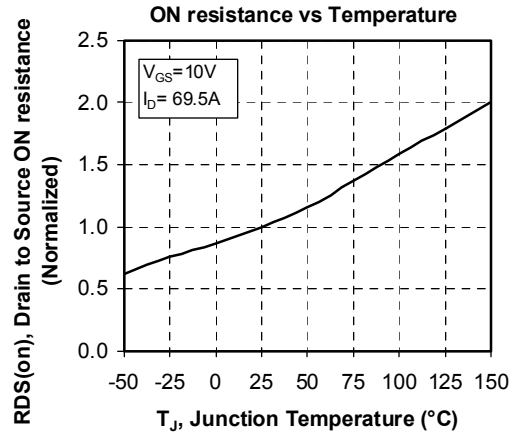
T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

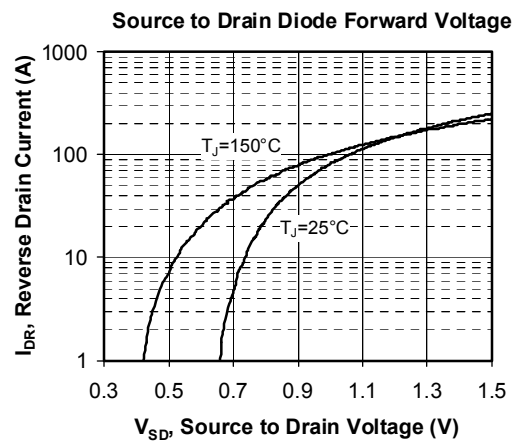
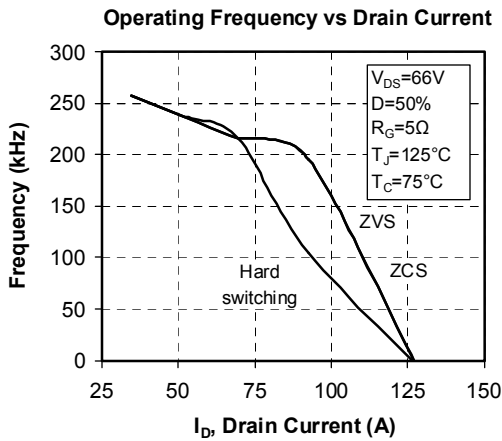
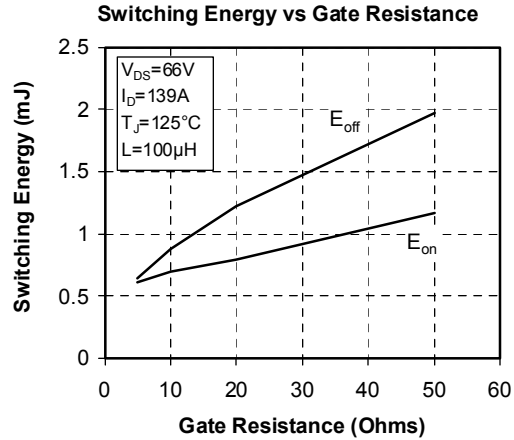
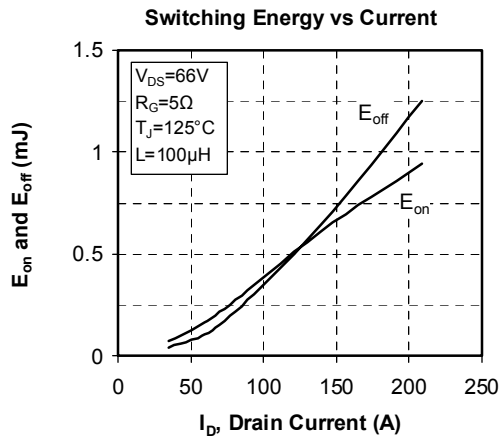
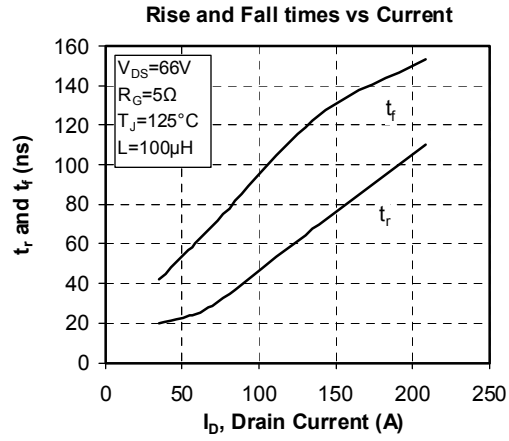
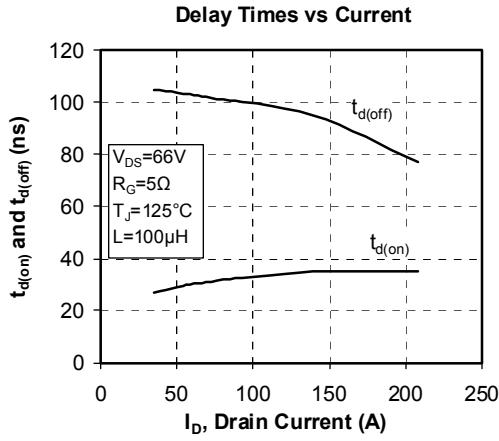
**Package outline** (dimensions in mm)



**Typical Performance Curve**







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